

REMARKS

Claims 1, 2 and 4-10 are pending in this application. Claim 10 has been newly added. Reconsideration of the rejections in view of these amendments and the following remarks is respectfully requested.

Rejections under 35 USC §103(a)

Claims 1, 2, 4, 9 and 5-8 stand rejected under 35 U.S.C. §103(a) as being obvious over Cantell et al (U.S. Patent No. 6,255,179) in view of the excerpt from Van Zant (*Microchip Fabrication*, 4th Ed., McGraw-Hill: New York, 2000, pp. 34, 172-173, 179-182).

Applicant respectfully traverses this rejection.

Claims 1 and 5 have been amended to recite “forming a refractory metal film and a TiN film on an entire surface of the silicon surface; and thermally treating in a nitrogen gas atmosphere so as to form forming a metal silicide film on a surface of the wiring by causing reaction between a surface layer of the thinned wiring and a refractory metal which reacts with silicon to form silicide.”

Cantell et al and Van Zant do not teach or suggest, among other things, these particular steps.

For at least these reasons, claims 1 and 5 patentably distinguish over the cited references. Claims 2, 4 and 9 depending from claim 1, and claims 6-8, depending from claim 5, also patentably distinguish over the cited references for at least the same reasons.

Thus, the 35 U.S.C. §103(a) rejection should be withdrawn.

New Claim

Newly added claim 10 is supported in the paragraph beginning at line 21 on page 7. In the embodiment described in this paragraph, the oxidation time is set to 20 seconds. Furthermore, the effect resulting from the short oxidation time is described. Therefore, the oxidation time of at most 20 seconds is supported in the specification.

The RTP that Van Zant teaches is used in the ion implant annealing step (page 179, the last sentence). Van Zant does not disclose that the RTP is used in the oxidation step. In claim 10, diffusion of impurities implanted in the substrate can be suppressed in the oxidation step by using RTP.

In view of the aforementioned amendments and accompanying remarks, claims as amended are in condition for allowance, which action, at an early date, is requested.

If, for any reason, it is felt that this application is not now in condition for allowance, the Examiner is requested to contact Applicant's undersigned attorney at the telephone number indicated below to arrange for an interview to expedite the disposition of this case.

U.S. Patent Application Serial No. 09/995,575

In the event that this paper is not timely filed, Applicant respectfully petitions for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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